

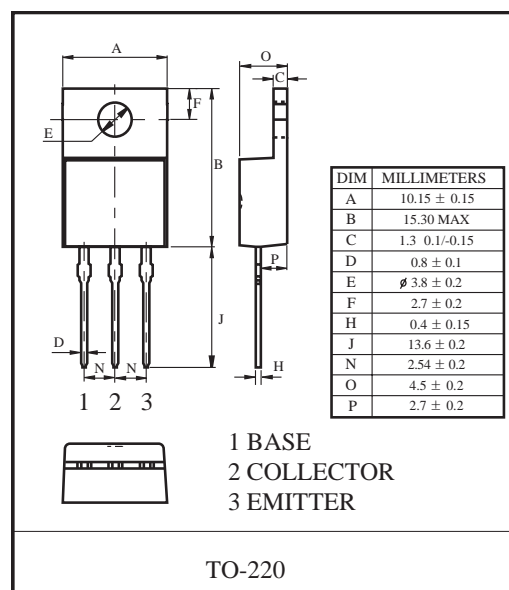
### TIP112 DARLINGTON TRANSISTOR (NPN)

#### FEATURES

- High DC Current Gain :  $h_{FE}=1000$  @  $V_{CE}=4V$ ,  $I_C=1A$ (Min.)
- Low Collector-Emitter Saturation Voltage
- Industrial Use

#### MAXIMUM RATINGS ( $T_a=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	2	A
$P_C$	Collector Power Dissipation	2	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55 to +150	$^\circ C$



#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10mA, I_E=0$	100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=30mA, I_B=0^{(SUS)}$	100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10mA, I_C=0$	5			V
Collector cut-off current	$I_{CEO}$	$V_{CE}=50V, I_B=0$			2	mA
Collector cut-off current	$I_{CBO}$	$V_{CB}=100V, I_E=0$			1	mA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			2	mA
DC current gain	$h_{FE(1)}$	$V_{CE}=4V, I_C=1A$	1000			
	$h_{FE(2)}$	$V_{CE}=4V, I_C=2A$	500			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2A, I_B=8mA$			2.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=4V, I_C=2A$			2.8	V
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=0.1MHz$			100	pF

## Typical Characteristics

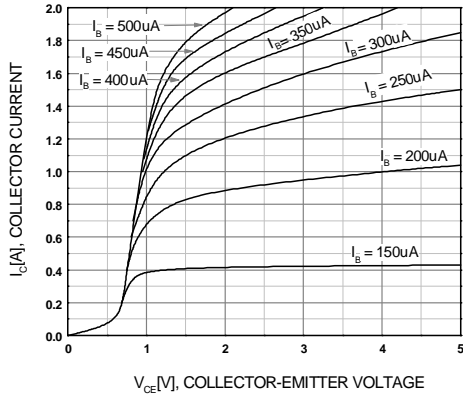


Figure 1. Static Characteristic

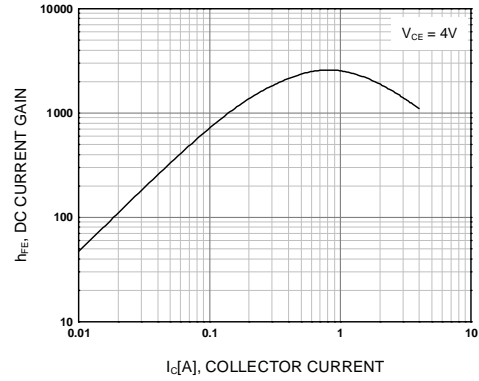


Figure 2. DC current Gain

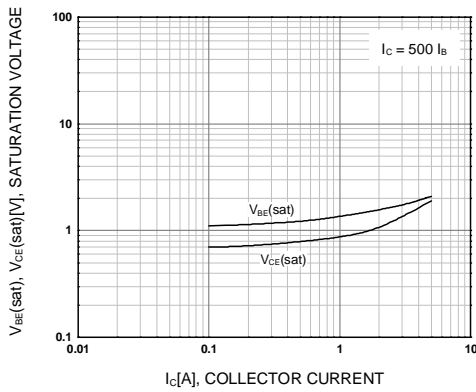


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

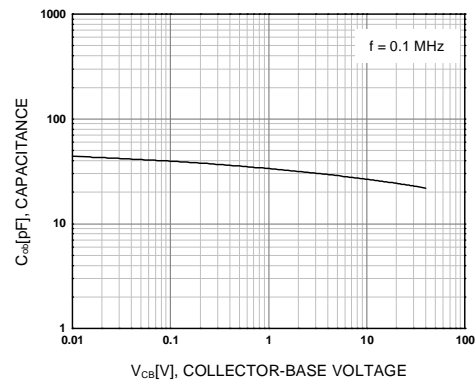


Figure 4. Collector Output Capacitance

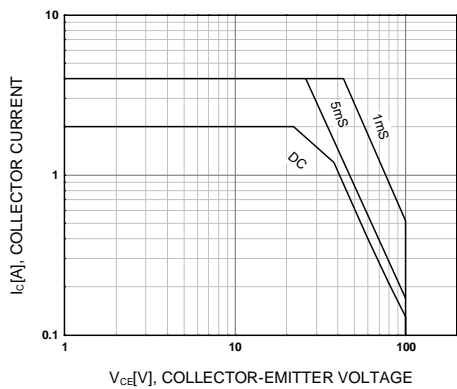


Figure 5. Safe Operating Area

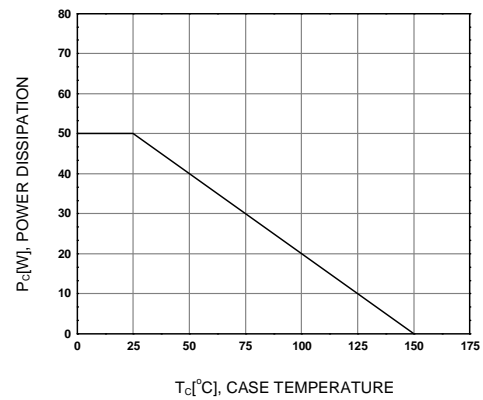


Figure 6. Power Derating